

### MACOM PURE CARBIDE

WSGPC04-V1

Rev. V2

#### **Features**

- Optimized for Cellular Base Station Applications
- Designed for Digital Predistortion Error Correction Systems
- High Terminal Impedances for Broadband Performance
- 48 V Capable Operation
- 100% RF Tested
- RoHS\* Compliant

### Description

The WSGPC04 GaN on SiC HEMT designed for base station applications and optimized for 2496 - 2690 MHz modulated signal operation. This device supports pulsed and linear operation with peak output power levels to 9.5 W (37.8 dBm) in an 4.0 x 4.5 mm DFN package.

### **Typical RF Performance**

WCDMA 3GPP TM1 64 DPCH 9.9 dB PAR @ 0.01% CCDF, V<sub>DS</sub> = 48 V, I<sub>DQ</sub> = 15 mA, T<sub>A</sub> = 25°C, P<sub>OUT</sub> = 24 dBm.

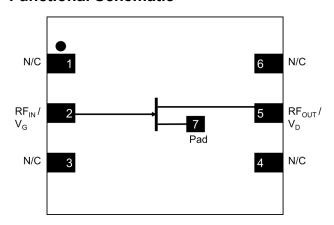
Frequency (MHz)	G <sub>P</sub> (dB)	η <sub>D</sub> (%)	OPAR (dB)	ACPR (dBc)
2496	19.3	13	10.3	-40
2690	18.1	12	10.2	-43

### **Ordering Information**

Part Number	Package
WSGPC04-V1-R3K	3000 Piece Reel
FXA-WSGPC04V1-1	Driver Sample Board (tuned for 2496-2690 MHz)
FXA-WSGPC04V1-2	Driver Sample Board (tuned for 2110-2170 MHz and 1805-1880 MHz)



#### **Functional Schematic**



#### **Pin Configuration**

Pin#	Function		
1,3,4,6 <sup>1</sup>	No Connection <sup>1</sup>		
2	RF Input / Gate		
5	RF Output / Drain		
7	Ground / Source		

 The pad on the package bottom must be connected to RF, DC and thermal ground.

<sup>\*</sup> Restrictions on Hazardous Substances, compliant to current RoHS EU directive.

# GaN on SiC Transistor 9.5 W, 48 V, Up to 5000 MHz



## MACOM PURE CARBIDE.

WSGPC04-V1

Rev. V2

RF Electrical Characteristics:  $T_A$  = 25°C,  $V_{DS}$  = 48 V,  $I_{DQ}$  = 15 mA Note: Performance in MACOM Single-ended Class-AB Evaluation Test Fixture, 50  $\Omega$  system.

Parameter	Test Conditions	Min.	Тур.	Max.	Units
Small Signal Gain	Pulsed <sup>2</sup> , 2690 MHz	-	18	-	dB
Saturation Output Power	Pulsed <sup>2</sup> , 2690 MHz	-	38	-	dBm
Power Gain	WCDMA <sup>3</sup> , 2690 MHz, P <sub>OUT</sub> = 24 dBm	-	18.8	-	dB
Drain Efficiency	WCDMA <sup>3</sup> , 2690 MHz, P <sub>OUT</sub> = 24 dBm	-	12.1	-	%
Output CCDF @ 0.01%	WCDMA <sup>3</sup> , 2690 MHz, P <sub>OUT</sub> = 24 dBm	-	10.1	-	dB
Adjacent Channel Power	WCDMA <sup>3</sup> , 2690 MHz, P <sub>OUT</sub> = 24 dBm	-	-43	-	dBc
Input Return Loss	WCDMA <sup>3</sup> , 2690 MHz, P <sub>OUT</sub> = 24 dBm	-	-14.9	-	dB
Ruggedness: Output Mismatch	All Phase Angles	VSWR = 5:1, No Device Damage		mage	

### RF Electrical Characteristics: $T_A$ = 25°C, $V_{DS}$ = 48 V, $I_{DQ}$ = 15 mA Note: Performance in MACOM Single-ended Class-AB Production Test Fixture, 50 $\Omega$ system.

Parameter	Test Conditions	Min.	Тур.	Max.	Units
Power Gain	LTE <sup>4</sup> , 2690 MHz, P <sub>OUT</sub> = 24 dBm	15.5	17.6	-	dB
Drain Efficiency	LTE <sup>4</sup> , 2690 MHz, P <sub>OUT</sub> = 24 dBm	12.5	14.7	-	%
Output CCDF @ 0.01%	LTE <sup>4</sup> , 2690 MHz, P <sub>OUT</sub> = 24 dBm	6.5	7.2	-	dB
Adjacent Channel Power Ratio	LTE <sup>4</sup> , 2690 MHz, P <sub>OUT</sub> = 24 dBm	-	-38	-34	dBc
Input Return Loss	LTE <sup>4</sup> , 2690 MHz, P <sub>OUT</sub> = 24 dBm	-	-13.7	-6	dB

<sup>2.</sup> Pulse details: 20 µs pulse width, 0.2 ms period, 10% Duty Cycle

<sup>3.</sup> Modulated Signal: 3.84 MHz, WCMDA 3GPP TM1 64 DPCH, 9.9 dB PAR @ 0.01% CCDF

<sup>4.</sup> LTE Signal: 20 MHz, 8 dB PAR @ 0.01% CCDF

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# MACOM PURE CARBIDE.

WSGPC04-V1

Rev. V2

DC Electrical Characteristics:  $T_A = 25$ °C

Parameter	Test Conditions	Min.	Тур.	Max.	Units
Drain-Source Leakage Current	V <sub>GS</sub> = -8 V, V <sub>DS</sub> = 150 V	-	-	0.53	mA
Gate-Source Leakage Current	V <sub>GS</sub> = -8 V, V <sub>DS</sub> = 150 V	-0.41	-	-	mA
Gate Threshold Voltage	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.2 mA	-3.8	-2.6	-2.1	V

## **Recommended Operating Voltages**

Parameter	Test Conditions	Min.	Тур.	Max.	Units
Drain Operating Voltage	_	0	-	50	V
Gate Quiescent Voltage	V <sub>DS</sub> = 48 V, I <sub>D</sub> = 15 mA	-3.6	-2.6	-2.1	V



## MACOM PURE CARBIDE.

WSGPC04-V1

Rev. V2

### **Absolute Maximum Ratings**<sup>5,6</sup>

Parameter	Absolute Maximum
Drain Source Voltage, $V_{DS}$	150 V
Gate Source Voltage, V <sub>GS</sub>	-10 V to +2 V
Operating Voltage	55 V
Gate Current I <sub>G</sub>	1.2 mA
Drain Current, I <sub>D</sub>	0.41 A
Junction Temperature	+225°C
Channel Operating Temperature	-40°C to +225°C
Storage Temperature	-65°C to +150°C

<sup>5.</sup> Exceeding any one or combination of these limits may cause permanent damage to this device.

### **Bias Sequencing**

#### **Bias ON**

- 1. Ensure RF is turned off
- 2. Apply pinch-off voltage of -5V to the gate
- 3. Apply nominal drain voltage
- 4. Bias gate to desired quiescent drain current
- 5. Apply RF

#### **Bias OFF**

- 1. Turn RF off
- 2. Apply pinch-off voltage to the gate
- 3. Turn off drain voltage
- 4. Turn-off gate voltage

#### **Handling Procedures**

Please observe the following precautions to avoid damage:

#### **Static Sensitivity**

These electronic devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

#### **ESD Characteristics**

Test Methodology	Test Conditions		
Human Body Model (per JS-001)	1A		

<sup>6.</sup> MACOM does not recommend sustained operation near these survivability limits.

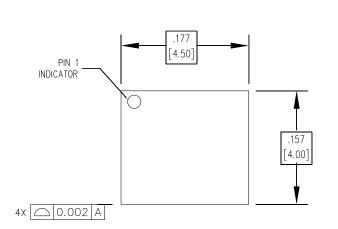


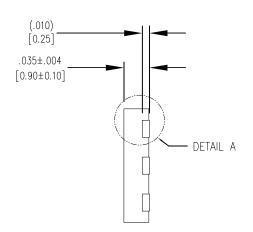
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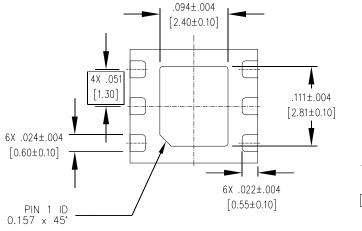
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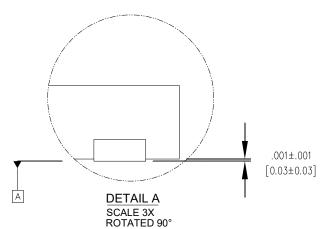
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# Lead-Free 4.0 x 4.5 mm 6-Lead Package Dimensions<sup>†</sup>









#### NOTES:

- 1. ALL DIMENSIONS SHOWN AS in [mm]. CONTROLLING DIMENSIONS ARE IN in. CONVERTED mm DIMENSIONS ARE NOT NECESSARILY EXACT.
- 2. EXPOSED LEADS 100% Sn MATTE.

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<sup>&</sup>lt;sup>†</sup> Meets JEDEC moisture sensitivity level (MSL) 3 requirements. Plating is Sn.

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Rev. V

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